## Spin-orbit coupling effects in CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> single crystals

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Single crystals of CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> were grown by the chemical transport reaction method using iodine as a transporting medium. The optical absorption peaks observed at 4132, 4332, 5970, 6329, 12 903, and 13 793 cm<sup>-1</sup> at 292 K can be explained in terms of the electronic transitions of Co<sup>2+</sup> ion in  $S_4$  symmetry. The crystal-field parameter Dq and the Racah parameter B were found to be 413 and 455 cm<sup>-1</sup>, respectively. Also the absorption spectrum of CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> single crystals obtained at 77 K in the 700-800-nm region was analyzed using  $S_4$  symmetry along with spin-orbit coupling effects.

CdGa<sub>2</sub>Se<sub>4</sub> is a tetrahedrally coordinated semiconductor crystallizing in the defect chalcopyrite structure. Its space group is  $S_4^2(I\overline{4})$ . It is known as an orderedvacancy compound having one-quarter of the cation sites unoccupied.<sup>1</sup> The structure of  $CdGa_2Se_4$  can be considered as a three-dimensional (3D) superstructure of zinc blende, i.e., doubling of the zinc-blende unit cell along the c axis results in the  $CdGa_2Se_4$  structure. Much attention has been paid to CdGa<sub>2</sub>Se<sub>4</sub> and its optical properties. Abdullaev et al.<sup>2</sup> reported the band-gap transitions in the fundamental absorption edge region. Optical absorption studies were done by Kshirsagar and Sinha.<sup>3</sup> Photoconductivity,<sup>4</sup> photoluminescence,<sup>5</sup> and Raman scattering<sup>6-8</sup> have been studied in CdGa<sub>2</sub>Se<sub>4</sub>. However, there exists no published results to date about the optical properties of  $CdGa_2Se_4$  doped with transition metals.

In this Brief Report we are going to present results on the crystal growth of CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> single crystals and its optical properties. In particular, the splittings of the highest energy level (<sup>4</sup>A and <sup>4</sup>E) of the Co<sup>2+</sup> ion in S<sub>4</sub> symmetry are analyzed in terms of the spin-orbit coupling effects in the CdGa<sub>2</sub>Se<sub>4</sub> host.

Single crystals of CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> were grown by the chemical transport reaction (CTR) method using iodine as a transporting medium. The charged ampoule was evacuated at  $\sim 1 \times 10^{-6}$  mm Hg, and the sealed ampoule was placed into a two-zone furnace at temperatures 750 to 900 °C. The single crystals of CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> grown had a lamella habit and an average size of  $4 \times 3 \times 1.5$  mm<sup>3</sup>. The crystal structure determined by x-ray diffraction analysis is a chalcopyrite structure with lattice constants a = 5.762 Å, c = 10.833 Å, which are in good agreement with the results obtained by Kshirsagar et al.<sup>3</sup> For optical measurements, the crystals of CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> were washed with ethyl alcohol in order to remove the iodine that has been physisorbed on the surface of the crystals. The absorption spectra were ob-

tained with a VIS-NIR spectrophotometer (Shimadzu MPS-5000) in the 700-2500-nm range and a monochromator (Jarrel Ash,  $f = \frac{1}{2}m$ ) in the 650-850-nm range. A cryogenic system (Air Products, CSA-202B) was used for low-temperature measurements.

The optical absorption spectrum of the Co-doped CdGa<sub>2</sub>Se<sub>4</sub> single crystals at 292 K in the near-infrared region is shown in Fig. 1. We observed six absorption peaks with energies 4132, 4332, 5970, 6329, 12 903, and 13 793 cm<sup>-1</sup> in the absorption regions which correspond to the transitions  ${}^{4}A_{2}({}^{4}F) \rightarrow {}^{4}T_{1}({}^{4}F), {}^{4}A_{2}({}^{4}F) \rightarrow {}^{4}T_{1}({}^{4}F), {}^{4}A_{2}({}^{4}F) \rightarrow {}^{4}T_{1}({}^{4}F), {}^{4}A_{2}({}^{4}F) \rightarrow {}^{4}T_{1}({}^{4}F)$  of the Co<sup>2+</sup> ion in various semiconductors with  $T_{d}$  symmetry. The splitting of the energy levels of the Co<sup>2+</sup> ion due to the reduction from  $T_{d}$  to  $S_{4}$  symmetry can be predicted by group theoretical calculations. The energy levels of  ${}^{4}T_{2}({}^{4}F), {}^{4}T_{1}({}^{4}F)$ , and  ${}^{4}T_{1}({}^{4}P)$  of Co<sup>2+</sup> in  $T_{d}$  symmetry are, respectively, split into two levels as reducing to a lower symmetry of



FIG. 1. Absorption spectrum of the CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> single crystals measured at 292 K in the 700-2500-nm region.

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 $S_4$ . Six absorption lines in Fig. 2 are assigned to the allowed transitions from the ground state  ${}^{4}B$  to the upper states of the  $Co^{2+}$  ion in  $S_4$  symmetry. These predictions are in good agreement with the results of the optical absorption spectrum measured in the Co-doped  $CdGa_2Se_4$  (see Figs. 1 and 2). As  $T_d$  symmetry is reduced to  $S_4$  symmetry, the spacing of the low-symmetry splitting of the  ${}^{4}T_{2}({}^{4}F)$  energy level is ~200 cm<sup>-1</sup>, which is similar to that of  $\sim 220$  cm<sup>-1</sup> obtained in a YAG:Co<sup>2+</sup> single crystal (YAG represents yttrium aluminum garnet).<sup>9</sup> Thus the observed absorption lines are well assigned to the electronic transitions between the split energy levels of the  $\mathrm{Co}^{2+}$  ion due to the reduction from  $T_d$  to S4 symmetry. The crystal field parameter Dq and the Racah parameter B, obtained from Fig. 1, are 413 and 455 cm<sup>-1</sup>, respectively. The Dq value in the Co-doped CdGa<sub>2</sub>Se<sub>4</sub> shows a good agreement with  $Dq = 460 \text{ cm}^{-1}$  for tetrahedral Co<sup>2+</sup> in the YAG:Co single crystal,<sup>9</sup> but shows considerable differences as compared with Dq = 830 cm<sup>-1</sup> for tetrahedral Co<sup>3+</sup>, Dq = 920 cm<sup>-1</sup> for octahedral Co<sup>2+</sup>, and Dq = 1600 $cm^{-1}$  for octahedral Co<sup>3+</sup> in the YAG:Co single crystal.9 Thus we can conclude that cobalt atoms in the CdGa<sub>2</sub>Se<sub>4</sub>:Co single crystal occupy the tetrahedral sites of the  $CdGa_2Se_4$  host lattice as  $Co^{2+}$  ions, then the reduction in symmetry is attributed to the cobalt atoms added to the CdGa<sub>2</sub>Se<sub>4</sub> host.

To identify the fine structure in the transition region centered at 13000 cm<sup>-1</sup>, the optical absorption spectrum of CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> single crystals was investigated at low temperatures. At 77 K we observed fourteen absorption peaks in the 12 500 to 14 200 cm<sup>-1</sup> region as shown in Fig. 3. If we consider  $S_4$  symmetry neglecting spin-orbit coupling, only two absorption lines are expected in these regions. Thus the observed results suggest that there exists the spin-orbit coupling effects of Co<sup>2+</sup> in  $S_4$  symmetry of CdGa<sub>2</sub>Se<sub>4</sub>. When the spin-orbit coupling effects are treated, using group theory, the ground state <sup>4</sup>B is split into two levels, and the first excited states are split into two levels for the <sup>4</sup>A state, four lev-



FIG. 2. Energy-level diagram for  $Co^{2+}$  due to the reduction in symmetry of the site from  $T_d$  to  $S_4$  symmetry.



FIG. 3. Absorption spectrum of the  $CdGa_2Se_4:Co^{2+}$  single crystal measured at 77 K in the 650 to 850-nm region.

els for <sup>4</sup>E state. Thus the lowering of symmetry from  $T_d$ to  $S_4$  along with spin-orbit coupling effects can be exhibited as twelve absorption lines due to the transitions of the Co<sup>2+</sup> ion from the ground state <sup>4</sup>B (doublet) to the upper states (doublet and quartet). The observed absorption spectrum of Fig. 3 is just what one would predict on the basis of the combined operation of  $S_4$  symmetry and spin-orbit coupling. From the energy values of the optical absorption peaks of the CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> single crystals, the energy levels of the Co<sup>2+</sup> ion in  $S_4$  symmetry



FIG. 4. Energy-level diagram for  $Co^{2+}$  in  $S_4$  symmetry with spin-orbit coupling predicted on the basis of group theory (the transition numbers correspond to the numbers of the optical absorption peaks in Fig. 3).

along with spin-orbit coupling effects can be plotted on the basis of group theory as shown in Fig. 4. The spinorbit splitting of the ground state <sup>4</sup>B obtained from Fig. 4 is the order of 35 cm<sup>-1</sup>, which is a reasonable value compared with that of about 30 cm<sup>-1</sup> in the YAG:Co<sup>2+</sup> crystal.<sup>9</sup> However, the optical absorption peaks at 12 269 (peak 0 of Fig. 3) and 13 913 cm<sup>-1</sup> (peak 00 of Fig. 3) cannot be explained by the spin-orbit coupling effects. It is considered that the unassigned transitions may relate to the defect levels which originate from the incorporation of cobalt atoms to the CdGa<sub>2</sub>Se<sub>4</sub>.

In summary, the optical absorption of the

CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> single crystals grown by the CTR method was investigated. The six absorption peaks observed at 292 K in the near-infrared region are attributed to the electronic transitions of Co<sup>2+</sup> between the localized energy levels. At 77 K, the observed absorption spectrum of the CdGa<sub>2</sub>Se<sub>4</sub>:Co<sup>2+</sup> single crystals in the 12 500 to 14 200 cm<sup>-1</sup> region was assigned in terms of  $S_4$  symmetry along with spin-orbit coupling effects.

The present studies were supported in part by the Basic Science Research Institute Program, Ministry of Education, 1987.

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